



### **40V N-Channel Enhancement Mode MOSFET**

Voltage

40 V

Current

10 A

### **Features**

- $R_{DS(ON)}$ ,  $V_{GS}@10V$ ,  $I_D@8A<11m\Omega$
- $R_{DS(ON)}$ ,  $V_{GS}@4.5V$ ,  $I_{D}@6A<15m\Omega$
- High switching speed
- Improved dv/dt capability
- Low Gate Charge
- Low reverse transfer capacitance
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

### **Mechanical Data**

- Case: SOP-8 package
- Terminals: Solderable per MIL-STD-750, Method 2026
- Approx. Weight: 0.0029 ounces, 0.083 grams

# 

# **Maximum Ratings and Thermal Characteristics** (T<sub>A</sub>=25 °C unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNITS	
Drain-Source Voltage		V <sub>DS</sub>	40	.,	
Gate-Source Voltage		$V_{GS}$	<u>+</u> 20	V	
Continuous Drain Current	T <sub>A</sub> =25°C		10		
	T <sub>A</sub> =70°C	l <sub>D</sub>	8	Α	
Pulsed Drain Current (Note 1)		I <sub>DM</sub>	40		
Power Dissipation	T <sub>A</sub> =25°C	P <sub>D</sub>	2.1	W	
	T <sub>A</sub> =70°C		1.3		
Operating Junction and Storage Temperature Range		T <sub>J</sub> ,T <sub>STG</sub>	-55~150	°C	
Typical Thermal Resistance - Junction to Ambient (Note 5)		$R_{ heta JA}$	59.5	°C/W	





# **Electrical Characteristics** (T<sub>A</sub>=25 °C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS		
Static								
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	$V_{GS}$ =0V, $I_D$ =250uA	40	-	-	V		
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$ , $I_{D}=250uA$	1.0	1.75	2.5			
Drain-Source On-State Resistance	R <sub>DS(on)</sub>	$V_{GS}$ =10V, $I_D$ =8A	-	9	11	mΩ		
Drain-Source On-State Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> =4.5V,I <sub>D</sub> =6A	-	11.5	15			
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =40V,V <sub>GS</sub> =0V	-	-	1.0	uA		
Gate-Source Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> = <u>+</u> 20V,V <sub>DS</sub> =0V	-	-	<u>+</u> 100	nA		
Dynamic (Note 6)								
Total Gate Charge	$Q_g$	V <sub>DS</sub> =20V, I <sub>D</sub> =10A, V <sub>GS</sub> =4.5V <sup>(Note 3)</sup>	-	10	-	nC		
Gate-Source Charge	$Q_gs$		-	3.5	-			
Gate-Drain Charge	$Q_{gd}$		-	3.6	-			
Input Capacitance	Ciss	V <sub>DS</sub> =20V, V <sub>GS</sub> =0V, f=1.0MHZ	-	1040	-	pF		
Output Capacitance	Coss		-	117	-			
Reverse Transfer Capacitance	Crss		-	84	-			
Turn-On Delay Time	td <sub>(on)</sub>	\/ 00\/ I 4A	-	9.4	-	ns		
Turn-On Rise Time	tr	$V_{DD}$ =20V, $I_{D}$ =1A, $V_{GS}$ =10V, $R_{G}$ =6 $\Omega$ (Note 3)	-	19	-			
Turn-Off Delay Time	td <sub>(off)</sub>		-	66	-			
Turn-Off Fall Time	tf		-	67	-			
Drain-Source Diode								
Maximum Continuous Drain-Source					10	Α		
Diode Forward Current	I <sub>S</sub>	is			10	A		
Diode Forward Voltage	$V_{SD}$	I <sub>S</sub> =1A, V <sub>GS</sub> =0V	-	0.7	1	V		

### NOTES:

- 1. Pulse width<300us, Duty cycle<2%.
- 2. Essentially independent of operating temperature typical characteristics.
- 3. The maximum current rating is package limited.
- 4. Repetitive rating, pulse width limited by junction temperature T<sub>J(MAX)</sub>=150°C. Ratings are based on low frequency and duty cycles to keep initial T<sub>J</sub> =25°C.
- 5. R<sub>OJA</sub> is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch<sup>2</sup> with 2oz.square pad of copper.
- 6. Guaranteed by design, not subject to production testing.





### TYPICAL CHARACTERISTIC CURVES

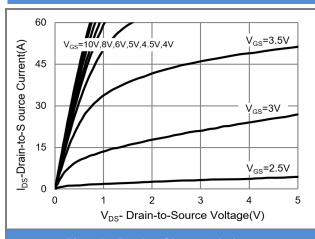
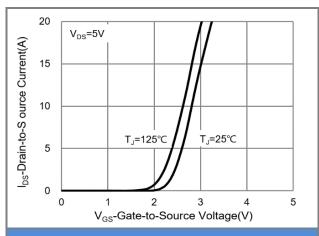


Fig.1 On-Region Characteristics



**Fig.2 Transfer Characteristics** 

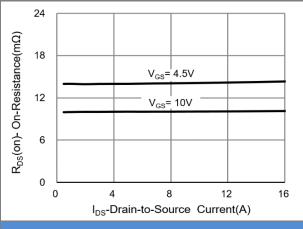


Fig.3 On-Resistance vs. Drain Current

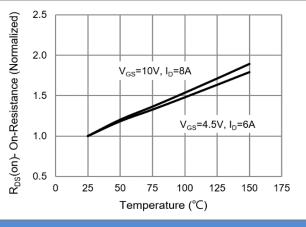


Fig.4 On-Resistance vs. Junction temperature

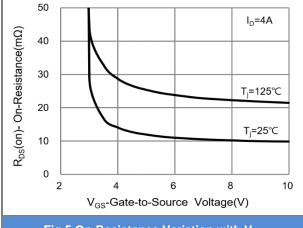


Fig.5 On-Resistance Variation with V<sub>GS</sub>

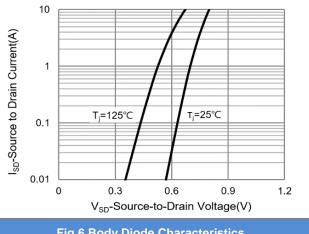


Fig.6 Body Diode Characteristics





### TYPICAL CHARACTERISTIC CURVES

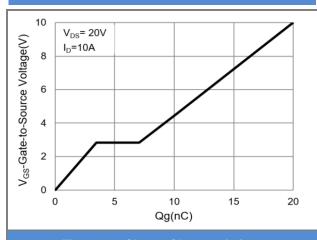


Fig.7 Gate-Charge Characteristics

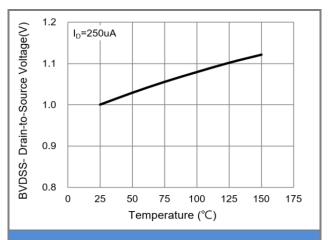


Fig.8 Breakdown Voltage Variation vs. Temperature

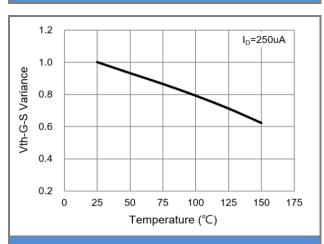


Fig.9 Threshold Voltage Variation with Temperature

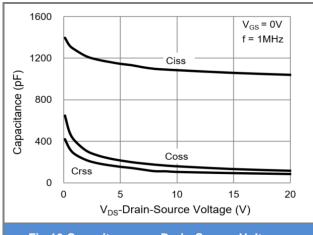
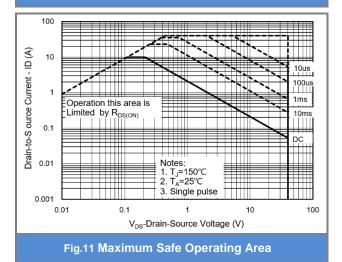


Fig.10 Capacitance vs. Drain-Source Voltage



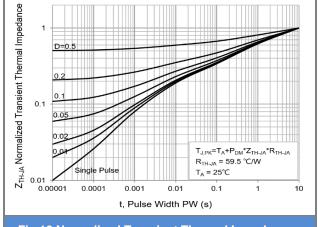


Fig.12 Normalized Transient Thermal Impedance

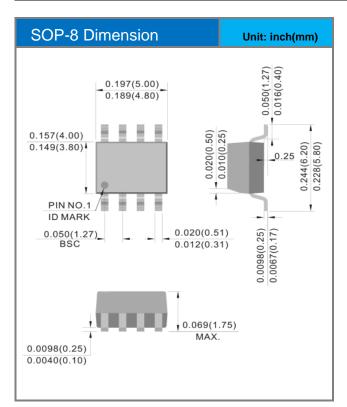


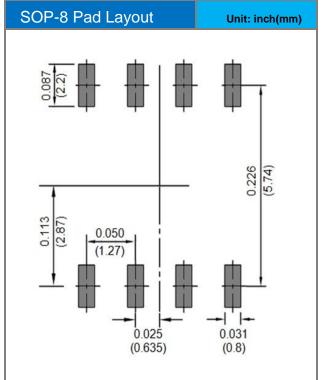


### **Part No Packing Code Version**

Part No Packing Code	Package Type	Packing Type	Marking	Version
PJL9426_R2_00001	SOP-8	2.5K pcs / 13" reel	L9426	Halogen free

## **Packaging Information & Mounting Pad Layout**









### Disclaimer

- Reproducing and modifying information of the document is prohibited without permission from Panjit International Inc..
- Panjit International Inc. reserves the rights to make changes of the content herein the document anytime without notification. Please refer to our website for the latest document.
- Panjit International Inc. disclaims any and all liability arising out of the application or use of any product including damages incidentally and consequentially occurred.
- Panjit International Inc. does not assume any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.
- Applications shown on the herein document are examples of standard use and operation. Customers are
  responsible in comprehending the suitable use in particular applications. Panjit International Inc. makes no
  representation or warranty that such applications will be suitable for the specified use without further testing or
  modification.
- The products shown herein are not designed and authorized for equipments requiring high level of reliability or relating to human life and for any applications concerning life-saving or life-sustaining, such as medical instruments, transportation equipment, aerospace machinery et cetera. Customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify Panjit International Inc. for any damages resulting from such improper use or sale.
- Since Panjit uses lot number as the tracking base, please provide the lot number for tracking when complaining.